

Method for evaluating initial stages of solid-state amorphization of interfaces in thin-film nanoscale Ni/Ti compositions comprises heating a sample, measuring electrical resistivity and determining a temperature coefficient of resistance based on which the solid-state amorphization is evaluated. Heating of the sample is carried out in a temperature range from 30 to 180°C at a constant rate. Values of the electrical resistivity are fixed during heating. Temperature coefficient of resistance is determined based on a dependence of a change in the electrical resistivity on a change in temperature.